Product data sheet

1. General description

NPN switching transistor in a medium power flat lead SOT89 (SC-62/TO-243) Surface-Mounted Device (SMD) plastic package.

PNP complement: PXT2907A

2. Features and benefits

High current: max. 600 mALow voltage: max. 40 V

3. Applications

Switching and linear amplification

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	600	mA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 150 mA; T_{amb} = 25 °C; $\delta \le 0.02$; $t_{p} \le 300 \ \mu s$; pulsed	100	-	300	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C
2	С	collector		в
3	В	base	3 2 1	,
			SOT89	sym123





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6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PXT2222A	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PXT2222A	%1P

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	600	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	800	mA
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.5	W
			[2]	-	0.8	W
			[3]	-	1.1	W
T_j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

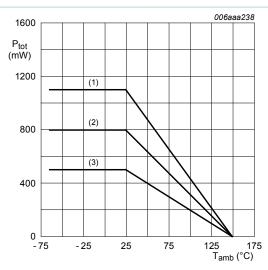
^[1] Transistor mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

PXT2222A

^[2] Transistor mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².

^[3] Transistor mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².

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- (1) FR4 PCB; 6 cm² mounting pad for collector.
- (2) FR4 PCB; 1 cm² mounting pad for collector.
- (3) FR4 PCB; standard footprint.

Fig. 1. Power derating curves

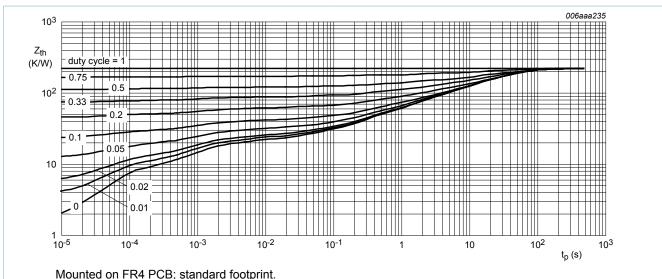
9. Thermal characteristics

Table 6. Thermal characteristics

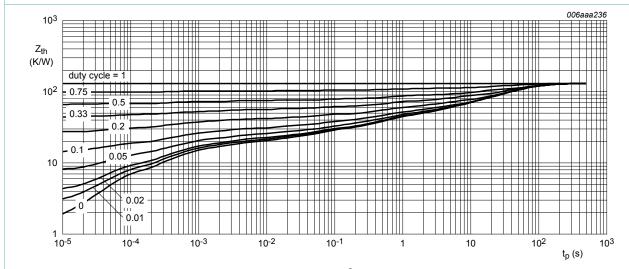
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance	om junction to	[1]	-	-	250	K/W
			<u>[2]</u>	-	-	156	K/W
	ambient		[3]	-	-	113	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

- [1] Transistor mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Transistor mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- [3] Transistor mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².

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Transient thermal impedance as a function of pulse time; typical values

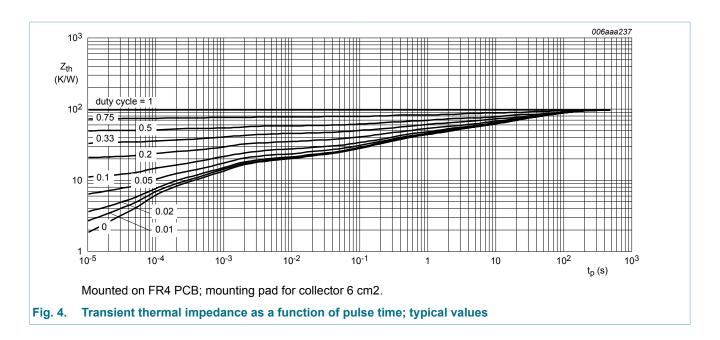


Mounted on FR4 PCB; mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance as a function of pulse time; typical values

Fig. 2.

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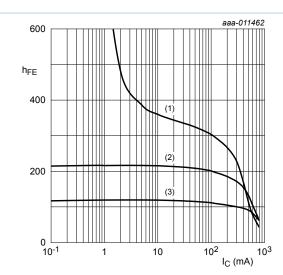
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Сво	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	10	nA
	current	V_{CB} = 60 V; I_{E} = 0 A; T_{j} = 125 °C	-	-	10	μA
EBO	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	10	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 0.1 mA; T_{amb} = 25 °C	35	-	-	
		V_{CE} = 10 V; I_{C} = 1 mA; T_{amb} = 25 °C	50	-	-	
		V_{CE} = 10 V; I_{C} = 10 mA; T_{amb} = 25 °C	75	-	-	
		V_{CE} = 10 V; I_{C} = 10 mA; T_{j} = -55 °C	35	-	-	
		V_{CE} = 1 V; I_{C} = 150 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	50	-	-	
		V_{CE} = 10 V; I_{C} = 150 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	100	-	300	
	V_{CE} = 10 V; I_{C} = 500 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	40	-	-		
V _{CEsat}	collector-emitter	I_C = 150 mA; I_B = 15 mA; T_{amb} = 25 °C	-	-	300	mV
saturation voltage		I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	-	-	1	V
V _{BEsat} base-emitter saturation	I_C = 150 mA; I_B = 15 mA; T_{amb} = 25 °C	0.6	-	1.2	V	
	voltage	I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	-	-	2	V
d	delay time	I _C = 150 mA; I _{Bon} = 15 mA;	-	-	15	ns
t _r	rise time	I _{Boff} = -15 mA; T _{amb} = 25 °C	-	-	20	ns
on	turn-on time		-	-	35	ns
·s	storage time		-	-	200	ns
l _f	fall time		-	-	60	ns
off	turn-off time		-	-	250	ns
Cc	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	8	pF
CE	emitter capacitance	V_{EB} = 500 mV; I_{C} = 0 A; i_{c} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	25	pF
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 20 mA; f = 100 MHz; T_{amb} = 25 °C	300	-	-	MHz
NF	noise figure	$V_{CE} = 5 \text{ V}; I_{C} = 200 \mu\text{A}; R_{S} = 2 k\Omega;$ $f = 1 \text{ kHz}; B = 200 \text{ Hz}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	4	dB

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$$V_{CE} = 10 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values

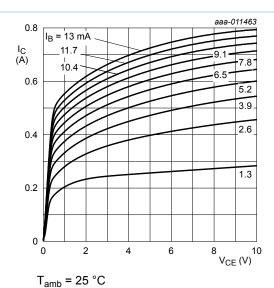
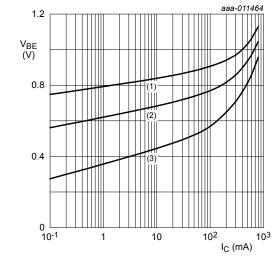


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



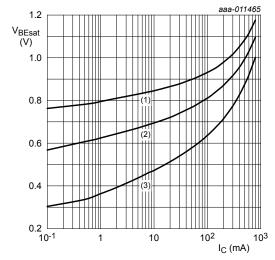
$$V_{CE} = 1 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

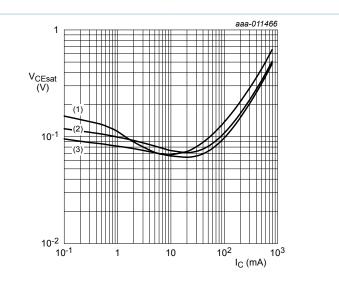
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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 $I_C/I_B = 10$

(1) T_{amb} = 150 °C

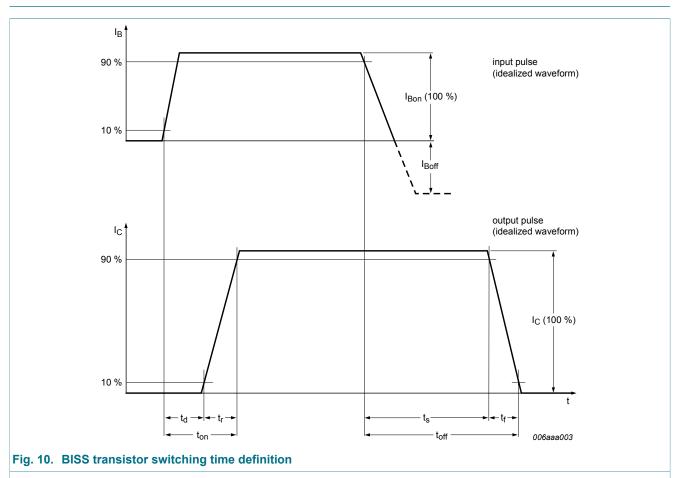
(2) T_{amb} = 25 °C

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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11. Test information



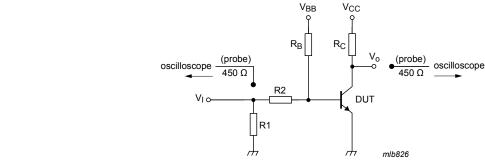
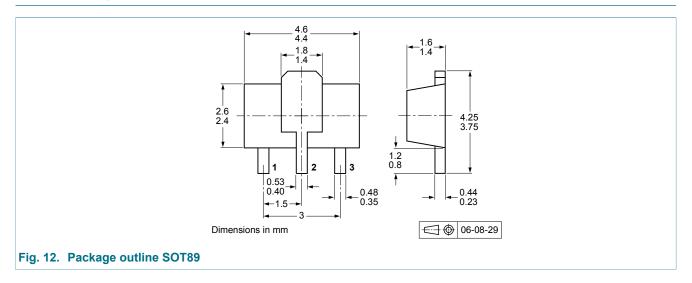


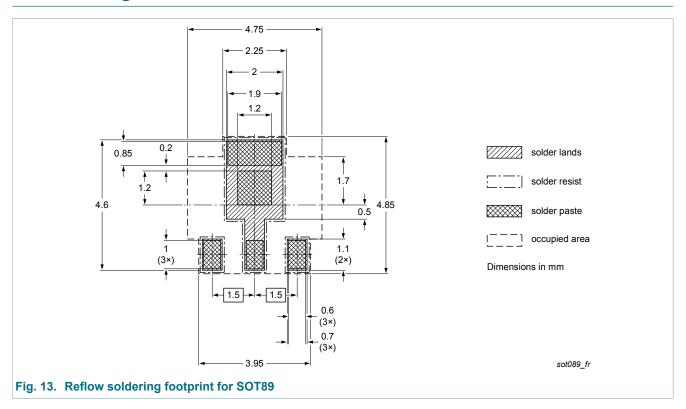
Fig. 11. Test circuit for switching times

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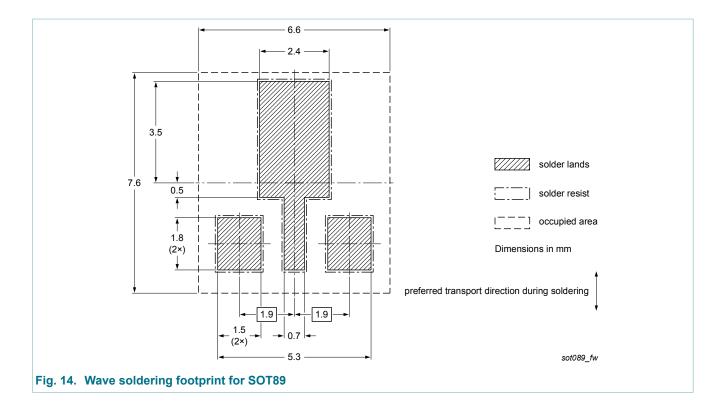
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PXT2222A v.5	20140402	Product data sheet	-	PXT2222A v.4	
Modifications:	of NXP Semiconduct Legal texts have be General description Quick refernce data Thermal characteris Limiting values: value	been adapted to the new company name where appropriate. icion: updated. lata: added. eristics: Figure 2 to 4 updated. values of I _C , I _{CM} and I _{BM} parameters corrected. Figures 5 to 9 added. ation: added.			
PXT2222A v.4	20041122	Product specification	-	PXT2222A v.3	
PXT2222A v.3	19990414	Product specification	-	PXT2222A v.2	
PXT2222A v.2	19970505	Product specification	-	PXT2222A v.1	
PXT2222A v.1	19940901	Product specification	-	-	

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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